VHF POWER MOSFET
N-Channel Enhancement Mode

DESCRIPTION:

The **ASI VFT5-28** is a N-Channel Enhancement-Mode RF Power MOSFET Designed for AM and FM Power Amplifier Applications up to 250 MHz.

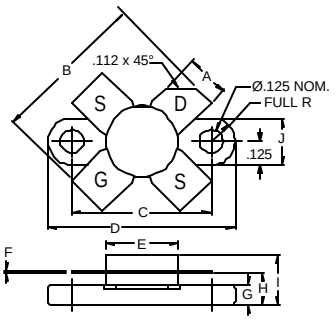
FEATURES INCLUDE:

- P_G = 14 dB Typical at 175 MHz
- **30:1 Load VSWR** Capability
- ***Omnigold***™ Metalization System

MAXIMUM RATINGS

I_D	1.0 A
V_{DSS}	60 V
V_{GS}	±40 V
P_{DISS}	17.5 W @ T_C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	10 °C/W

PACKAGE STYLE .380 4L FLG



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.220 / 5.59	.230 / 5.84
B	.785 / 19.94	
C	.720 / 18.29	.730 / 18.54
D	.970 / 24.64	.980 / 24.89
E		.385 / 9.78
F	.004 / 0.10	.006 / 0.15
G	.085 / 2.16	.105 / 2.67
H	.160 / 4.06	.180 / 4.57
I		.280 / 7.11
J	.240 / 6.10	.255 / 6.48

ASI ORDER CODE: ASI10701

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{DSS}	I_D = 5 mA			60			V
I_{DSS}	V_{DS} = 28 V	V_{GS} = 0 V				1.0	mA
I_{GSS}	V_{DS} = 0 V	V_{GS} = 20 V				1.0	µA
$V_{GS(th)}$	I_D = 25 mA	V_{DS} = 10 V		1.0		6.0	V
g_{fs}	I_D = 250 mA	V_{DS} = 10 V		80			mS
C_{iss} C_{oss} C_{rss}	V_{DS} = 28 V	V_{GS} = 0 V	f = 1.0 MHz		9.0 7.0 1.0		pF
P_G η_D	V_{DD} = 50 V F = 175 MHz	I_{DQ} = 50 mA	P_{out} = 5.0 W	13 50	14 60		dB %
ψ	V_{SWR} = 30:1 AT ALL PHASE ANGLES			NO DEGRADATION IN OUTPUT POWER			

Specifications are subject to change without notice.